# 2SD1890

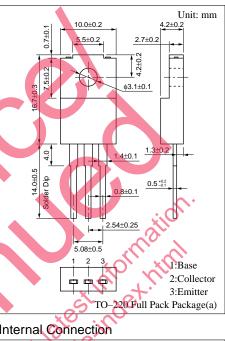
### Silicon NPN triple diffusion planar type Darlington

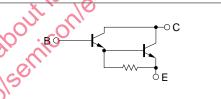
For power amplification Complementary to 2SB1250

## Features

- Optimum for 25W HiFi output •
- High foward current transfer ratio  $h_{FE}$ : 5000 to 30000 •
- Low collector to emitter saturation voltage  $V_{CE(sat)}$ : <2.5V
- Full-pack package which can be installed to the heat sink with • one screw

Absolute Maximu	m Ratings	$(T_C = 25^{\circ}C)$		Solde
Parameter	Symbol	Ratings	Unit	μ
Collector to base voltage	V <sub>CBO</sub>	100	V	5
Collector to emitter voltage	V <sub>CEO</sub>	80	V	
Emitter to base voltage	V <sub>EBO</sub>	5	V	
Peak collector current	I <sub>CP</sub>	6	A	
Collector current	I <sub>C</sub>	3	A	Internal Conn
Collector power T <sub>C</sub> =25°C		35		
dissipation Ta=25°C	P <sub>C</sub>	2	W	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	Y CON
			J.	
Electrical Charac	teristics (T <sub>c</sub>	=25°C)	in or	). <del> </del>
Parameter	Syr	nbol	Conditions	min
	Ісво	VCBE	100V, $I_E \equiv 0$	
Collector cutoff current	1		8000-0	



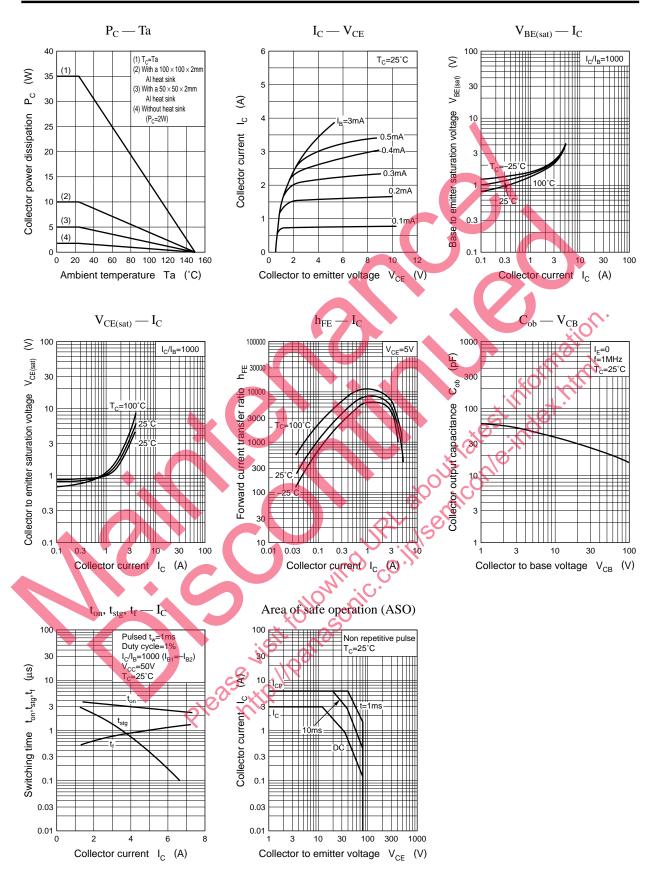


#### Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	Ісво	$V_{CB} \equiv 100V, I_E \neq 0$			100	μΑ
	I <sub>CEO</sub>	$V_{CE} = 80 V I_B = 0$			100	μA
Emitter cutoff current	I <sub>EBO</sub>	$V_{\rm EB} = 5$ V, $I_{\rm C} = 0$			100	μΑ
Collector to emitter voltage	V <sub>CEQ</sub>	$I_{\rm C} = 30 {\rm mA}, I_{\rm B} = 0$	80			V
Forward current transfer ratio	h <sub>FE</sub>	$V_{\rm CE} = 5$ V, $I_{\rm C} = 1$ A	2000			
	h <sub>FE2</sub> *	$V_{CE} = 5V, I_C = 2A$	5000		30000	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 2$ A, $I_{\rm B} = 2$ mA			2.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 2$ A, $I_{\rm B} = 2$ mA			3.0	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10V, I_C = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t <sub>on</sub>	$I_{C} = 2A, I_{B1} = 2mA, I_{B2} = -2mA,$		3.5		μs
Storage time	t <sub>stg</sub>			2.5		μs
Fall time	t <sub>f</sub>	$V_{CC} = 50V$		0.6		μs

#### <sup>\*</sup>h<sub>FE2</sub> Rank classification

Rank	Q	Р		
h <sub>FE2</sub>	5000 to 15000	8000 to 30000		





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